

SN74AVC4T774-Q1 構成可能な電圧レベルシフト機能と 3 ステート出力 (独立した方向制御入力付き) を備えた車載用 4 ビット デュアル電源バストランシーバ

1 特長

- 車載アプリケーション認定済み
- 以下の結果で AEC-Q100 認定済み:
 - デバイス温度: 動作時周囲温度範囲 -40°C ~ 125°C
 - デバイス HBM ESD 分類レベル H3B (JES-001)
 - デバイス CDM ESD 分類レベル C5 (JESD 22 C101)
- 機能安全対応
- V_{CCA} 電圧基準の制御入力 V_{IH}/V_{IL} レベル
- 完全に構成可能なデュアル レール設計により、1.08V ~ 3.6V の電源電圧の全範囲にわたって各ポートが動作可能
- I/O は 4.6V 許容です
- I_{off} により部分的パワーダウン モードでの動作をサポート
- 最大データレート:
 - 500Mbps (1.08V から 3.6V への変換)
- JESD 78, Class II 準拠で 100mA 超のラッチアップ性能

2 アプリケーション

- テレマティクス
- クラスタ
- ヘッド ユニット
- ナビゲーション システム

3 概要

この 4 ビット非反転バストランシーバは、設定可能な 2 本の独立した電源レールを使用します。A ポートは V_{CCA} に追従するように設計されています。V_{CCA} ピンには、1.08V ~ 3.6V の電源電圧を入力できます。B ポートは、V_{CCB} に追従する設計になっています。V_{CCB} には、1.08V ~ 3.6V の電源電圧を入力できます。これにより、1.2V、1.5V、1.8V、2.5V、3.3V の任意の電圧ノード間での自在な低電圧双方向変換が可能です。

SN74AVC4T774-Q1 は、2 つのデータ バス間の非同期通信用に設計されています。方向制御 (DIR) 入力および出力イネーブル ($\overline{OE}$) 入力のロジックレベルに応じて、B ポート出力もしくは A ポート出力のいずれかがアクティブになるか、または、両方の出力ポートが高インピーダンスモードになります。本デバイスは、B ポート出力がアクティブになった場合、A バスから B バスへデータを転送し、A ポート出力がアクティブになった場合、B バスから A バスへデータを転送します。A ポートと B ポートの入力回路はどちらも常にアクティブであるため、これらのポートには論理 High または Low レベルを印加して、I_{cc} と I_{ccz} が過剰に流れないようにする必要があります。

SN74AVC4T774-Q1 は、制御ピン (DIR1、DIR2、DIR3、DIR4、 $\overline{OE}$) が V_{CCA} から電源を供給されるように設計されています。

このデバイスは、I_{off} を使用する部分的パワーダウン アプリケーション用の動作が完全に規定されています。I_{off} 回路で出力をディセーブルすることにより、電源切断時にデバイスに電流が逆流して損傷するのを回避できます。

この V_{CC} 絶縁機能の設計により、いずれかの V_{CC} 入力がある GND の場合、両方のポートが高インピーダンス状態になります。

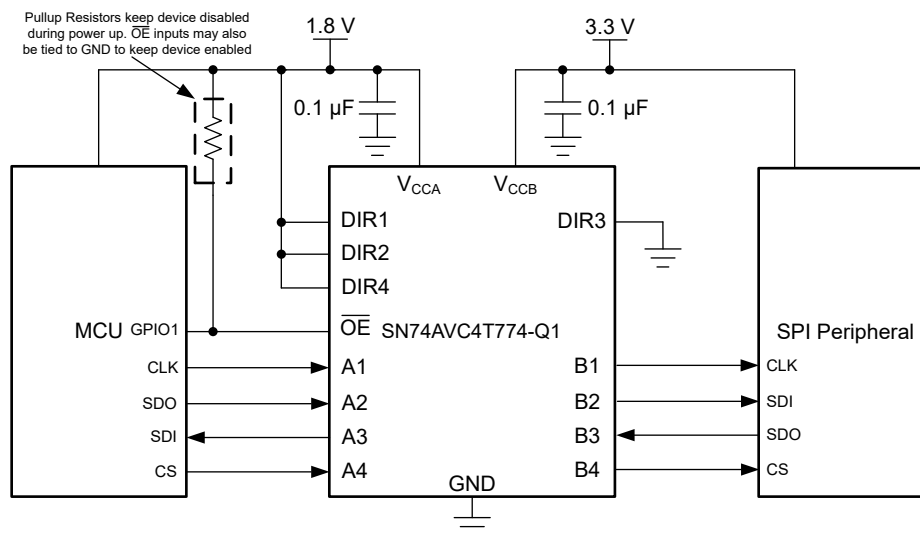
電源投入または電源オフの間にデバイスを高インピーダンス状態にするには、 $\overline{OE}$ をプルアップ抵抗を介して V_{CC} に接続します。この抵抗の最小値は、ドライバの電流シンク能力によって決まります。

パッケージ情報

部品番号	パッケージ ⁽¹⁾	パッケージ サイズ ⁽²⁾
SN74AVC4T774-Q1	PW (TSSOP, 16)	5mm × 6.4mm
	BQB (WQFN, 16)	3.5mm × 2.5mm
	DYY (SOT, 16)	4.2mm × 2mm

- 詳細については、[セクション 11](#) を参照してください。
- パッケージ サイズ (長さ × 幅) は公称値であり、該当する場合はピンも含まれます。



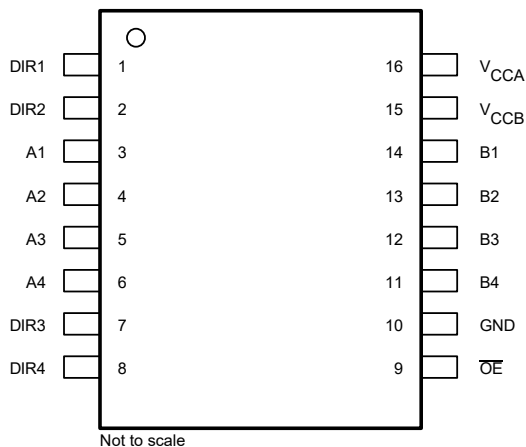


代表的なアプリケーション回路図 SN74AVC4T774-Q1

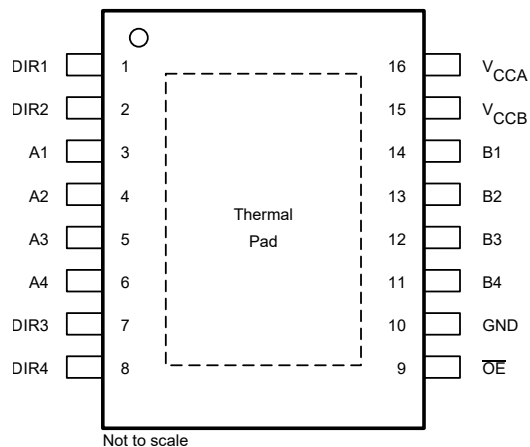
Table of Contents

1 特長	1	7.1 Overview.....	18
2 アプリケーション	1	7.2 Functional Block Diagram.....	18
3 概要	1	7.3 Feature Description.....	18
4 Pin Configuration and Functions	4	7.4 Device Functional Modes.....	18
5 Specifications	6	8 Application and Implementation	19
5.1 Absolute Maximum Ratings.....	6	8.1 Application Information.....	19
5.2 ESD Ratings.....	6	8.2 Typical Application.....	19
5.3 Recommended Operating Conditions	6	8.3 Power Supply Recommendations.....	20
5.4 Thermal Information.....	7	8.4 Layout.....	21
5.5 Electrical Characteristics	7	9 Device and Documentation Support	22
5.6 Switching Characteristics: $V_{CCA} = 1.2V \pm 0.12V$	9	9.1 Documentation Support.....	22
5.7 Switching Characteristics: $V_{CCA} = 1.5V \pm 0.1V$	10	9.2 ドキュメントの更新通知を受け取る方法.....	22
5.8 Switching Characteristics: $V_{CCA} = 1.8V \pm 0.15V$	11	9.3 サポート・リソース.....	22
5.9 Switching Characteristics: $V_{CCA} = 2.5V \pm 0.2V$	12	9.4 Trademarks.....	22
5.10 Switching Characteristics: $V_{CCA} = 3.3V \pm 0.3V$	13	9.5 静電気放電に関する注意事項.....	22
5.11 Operating Characteristics.....	14	9.6 用語集.....	22
5.12 Typical Characteristics.....	15	10 Revision History	22
6 Parameter Measurement Information	17	11 Mechanical, Packaging, and Orderable Information	23
7 Detailed Description	18		

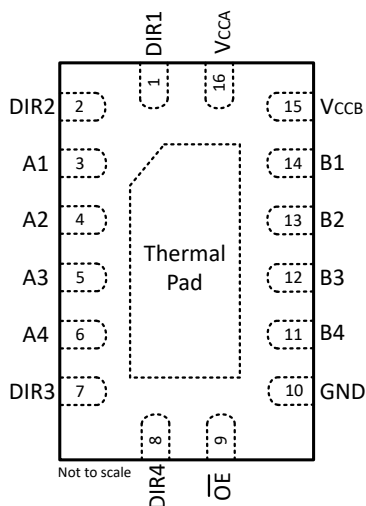
4 Pin Configuration and Functions



✎ 4-1. PW Package, 16-Pin TSSOP
(Top View)



✎ 4-2. DYY Package, 16-Pin SOT
(Top View)



✎ 4-3. BQB Package, 16-Pin WQFN
(Top View)

表 4-1. Pin Functions

PIN		TYPE ⁽¹⁾	DESCRIPTION
NAME	NO.		
DIR1	1	I	Controls signal flow for the first (A1/B1) I/O channels. Direction-control input referenced to V _{CCA}
DIR2	2	I	Controls signal flow for the second (A2/B2) I/O channels. Direction-control input referenced to V _{CCA}
A1	3	I/O	Input/output A1. Referenced to V _{CCA}
A2	4	I/O	Input/output A2. Referenced to V _{CCA} .
A3	5	I/O	Input/output A3. Referenced to V _{CCA} .
A4	6	I/O	Input/output A4. Referenced to V _{CCA} .
DIR3	7	I	Controls signal flow for the third (A3/B3) I/O channels. Direction-control input referenced to V _{CCA}
DIR4	8	I	Controls signal flow for the fourth (A4/B4) I/O channels. Direction-control input referenced to V _{CCA}
$\overline{OE}$	9	I	3-state output-mode enables. Pull $\overline{OE}$ high to place all outputs in 3-state mode. Referenced to V _{CCA} .
GND	10	G	Ground
B4	11	I/O	Input/output B4. Referenced to V _{CCB} .
B3	12	I/O	Input/output B3. Referenced to V _{CCB} .
B2	13	I/O	Input/output B2. Referenced to V _{CCB} .
B1	14	I/O	Input/output B1. Referenced to V _{CCB} .
V _{CCB}	15	P	B-port supply voltage. $1.08V \leq V_{CCB} \leq 3.6V$
V _{CCA}	16	P	A-port supply voltage. $1.08V \leq V_{CCA} \leq 3.6V$
Thermal pad		—	The exposed thermal pad must be connected as a secondary GND or be left electrically open.

(1) I = input, O = output, P = Power, G = Ground

5 Specifications

5.1 Absolute Maximum Ratings

over operating ambient temperature range (unless otherwise noted) ⁽¹⁾

			MIN	MAX	UNIT
V_{CCA} V_{CCB}	Supply voltage		–0.5	4.6	V
V_I	Input voltage ⁽²⁾	I/O ports (A port)	–0.5	4.6	V
		I/O ports (B port)	–0.5	4.6	
		Control inputs	–0.5	4.6	
V_O	Voltage applied to any output in the high-impedance or power-off state ⁽²⁾	A port	–0.5	4.6	V
		B port	–0.5	4.6	
V_O	Voltage applied to any output in the high or low state ^{(2) (3)}	A port	–0.5	$V_{CCA} + 0.5$	V
		B port	–0.5	$V_{CCB} + 0.5$	
I_{IK}	Input clamp current	$V_I < 0$		–50	mA
I_{OK}	Output clamp current	$V_O < 0$		–50	mA
I_O	Continuous output current			±50	mA
	Continuous current through V_{CCA} , V_{CCB} , or GND			±100	mA
T_{stg}	Storage temperature		–65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) The input voltage and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.

(3) The output positive-voltage rating may be exceeded up to 4.6V maximum if the output current rating is observed.

5.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins ⁽¹⁾	±8000	V
		Charged device model (CDM), per JEDEC specification JESD22-C101, all pins	±1000	
		Machine model (C101)	±150	

(1) AEC Q100-002 indicates HBM stressing is done in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

5.3 Recommended Operating Conditions

			V _{CCI}	V _{CCO}	MIN	MAX	UNIT
V _{CCA}	Supply voltage				1.08	3.6	V
V _{CCB}	Supply voltage				1.08	3.6	V
V _{IH}	High-level input voltage	Data inputs ⁽¹⁾	1.08V		V _{CCI} × 0.7		V
			1.2V to 1.95V		V _{CCI} × 0.65		
			2V to 2.7V		1		
			2.8V to 3.6V		1.4		
V _{IL}	Low-level input voltage	Data inputs ⁽¹⁾	1.08V		V _{CCI} × 0.3		V
			1.1V to 1.95V		V _{CCI} × 0.35		
			2V to 2.7V		1.5		
			3V to 3.6V		1.9		
V _{IH}	High-level input voltage	DIR (referenced to V _{CCA}) ⁽²⁾	1.08V to 1.95V		V _{CCA} × 0.65		V
			2V to 2.7V		1		
			3V to 3.6V		1.3		

5.3 Recommended Operating Conditions (続き)

			V _{CCI}	V _{CCO}	MIN	MAX	UNIT
V _{IL}	Low-level input voltage	DIR (referenced to V _{CCA}) ⁽²⁾	1.08V to 1.95V		V _{CCA} × 0.35		V
			2V to 2.7V		1.3		
			3V to 3.6V		1.7		
V _I	Input voltage				0	3.6	V
V _O	Output voltage	Active state			0	V _{CCO}	V
		3-state			0	3.6	
I _{OH}	High-level output current			1.08V to 1.32V	−3		mA
				1.4V to 1.6V	−6		
				1.65V to 1.95V	−8		
				2.3V to 2.7V	−9		
				3V to 3.6V	−12		
I _{OL}	Low-level output current			1.08V to 1.32V	3		mA
				1.4V to 1.6V	6		
				1.65V to 1.95V	8		
				2.3V to 2.7V	9		
				3V to 3.6V	12		
Δt/Δv	Input transition rise or fall rate				5		ns/V
T _A	Operating ambient temperature				−40	125	°C

(1) For V_{CCI} values not specified in the data sheet, V_{IH} min = V_{CCI} × 0.7V, V_{IL} max = V_{CCI} × 0.3V

(2) For V_{CCI} values not specified in the data sheet, V_{IH} min = V_{CCA} × 0.7V, V_{IL} max = V_{CCA} × 0.3V

5.4 Thermal Information

THERMAL METRIC ⁽¹⁾		SN74AVC4T774-Q1			UNIT
		PW (TSSOP)	BQB (WQFN)	DYY (SOT)	
		16 PINS	16 PINS	16 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	123.8	79.9	163.4	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	58.3	77.5	90.0	°C/W
R _{θJB}	Junction-to-board thermal resistance	81.7	49.0	93.1	°C/W
Ψ _{JT}	Junction-to-top characterization parameter	6.7	7.3	10.9	°C/W
Ψ _{JB}	Junction-to-board characterization parameter	80.9	49.0	92.1	°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	26.4	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

5.5 Electrical Characteristics

All typical limits apply over T_A = 25°C, and all maximum and minimum limits apply over T_A = –40°C to 125°C (unless otherwise noted).^{(1) (2)}

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
V _{OH}	I _{OH} = −100μA; V _{CCA} = 1.08V to 3.6V; V _{CCB} = 1.08V to 3.6V; V _I = V _{IH}	V _{CCO} − 0.2			V
	I _{OH} = −3mA; V _{CCA} = 1.1V; V _{CCB} = 1.1V; V _I = V _{IH}	0.8			
	I _{OH} = −6mA; V _{CCA} = 1.4V; V _{CCB} = 1.4V; V _I = V _{IH}	1			
	I _{OH} = −8mA; V _{CCA} = 1.65V; V _{CCB} = 1.65V; V _I = V _{IH}	1.2			
	I _{OH} = −9mA; V _{CCA} = 2.3V; V _{CCB} = 2.3V; V _I = V _{IH}	1.8			
	I _{OH} = −12mA; V _{CCA} = 3V; V _{CCB} = 3V; V _I = V _{IH}	2.3			

5.5 Electrical Characteristics (続き)

All typical limits apply over $T_A = 25^\circ\text{C}$, and all maximum and minimum limits apply over $T_A = -40^\circ\text{C}$ to 125°C (unless otherwise noted).^{(1) (2)}

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
V_{OL}		$I_{OL} = 100\mu\text{A}$; $V_{CCA} = 1.08\text{V}$ to 3.6V ; $V_{CCB} = 1.08\text{V}$ to 3.6V ; $V_I = V_{IL}$			0.2	V
		$I_{OL} = 3\text{mA}$; $V_{CCA} = 1.1\text{V}$; $V_{CCB} = 1.1\text{V}$; $V_I = V_{IL}$			0.2	
		$I_{OL} = 6\text{mA}$; $V_{CCA} = 1.4\text{V}$; $V_{CCB} = 1.4\text{V}$; $V_I = V_{IL}$			0.31	
		$I_{OL} = 8\text{mA}$; $V_{CCA} = 1.65\text{V}$; $V_{CCB} = 1.65\text{V}$; $V_I = V_{IL}$			0.35	
		$I_{OL} = 9\text{mA}$; $V_{CCA} = 2.3\text{V}$; $V_{CCB} = 2.3\text{V}$; $V_I = V_{IL}$			0.33	
		$I_{OL} = 12\text{mA}$; $V_{CCA} = 3\text{V}$; $V_{CCB} = 3\text{V}$; $V_I = V_{IL}$			0.40	
I_I	DIR input	$V_I = V_{CCA}$ or GND; $V_{CCA} = 1.08\text{V}$ to 3.6V ; $V_{CCB} = 1.08\text{V}$ to 3.6V	$T_A = 25^\circ\text{C}$	-0.25	0.25	μA
			$T_A = -40^\circ\text{C}$ to 125°C	-1	1.5	
I_{off}	A port	V_I or $V_O = 0$ to 3.6V ; $V_{CCA} = 0\text{V}$; $V_{CCB} = 0\text{V}$ to 3.6V	$T_A = 25^\circ\text{C}$	± 0.1	± 1	μA
			$T_A = -40^\circ\text{C}$ to 125°C		± 5	
	B port	V_I or $V_O = 0$ to 3.6V ; $V_{CCA} = 0\text{V}$ to 3.6V ; $V_{CCB} = 0\text{V}$	$T_A = 25^\circ\text{C}$	± 0.1	± 1	
			$T_A = -40^\circ\text{C}$ to 125°C		± 5	
I_{OZ} ⁽³⁾	A or B port	$V_O = V_{CCO}$ or GND, $V_I = V_{CCI}$ or GND; $\overline{OE} = V_{IH}$; $V_{CCA} = 3.6\text{V}$; $V_{CCB} = 3.6\text{V}$	$T_A = 25^\circ\text{C}$	± 0.5	± 2.5	μA
			$T_A = -40^\circ\text{C}$ to 125°C		± 5	
	B port	$V_O = V_{CCO}$ or GND, $V_I = V_{CCI}$ or GND; $\overline{OE} = \text{don't care}$; $V_{CCA} = 0\text{V}$; $V_{CCB} = 3.6\text{V}$			± 5	
	A port	$V_O = V_{CCO}$ or GND, $V_I = V_{CCI}$ or GND; $\overline{OE} = \text{don't care}$; $V_{CCA} = 3.6\text{V}$; $V_{CCB} = 0\text{V}$			± 5	
I_{CCA}		$V_I = V_{CCI}$ or GND, $I_O = 0$	$V_{CCA} = 1.08\text{V}$ to 3.6V $V_{CCB} = 1.08\text{V}$ to 3.6V		9	μA
			$V_{CCA} = 0\text{V}$; $V_{CCB} = 3.6\text{V}$		-2	
			$V_{CCA} = 3.6\text{V}$; $V_{CCB} = 0\text{V}$		5	
I_{CCB}		$V_I = V_{CCI}$ or GND, $I_O = 0$	$V_{CCA} = 1.08\text{V}$ to 3.6V $V_{CCB} = 1.08\text{V}$ to 3.6V		7	μA
			$V_{CCA} = 0\text{V}$; $V_{CCB} = 3.6\text{V}$		4.5	
			$V_{CCA} = 3.6\text{V}$; $V_{CCB} = 0\text{V}$		-2	
$I_{CCA} + I_{CCB}$		$V_I = V_{CCI}$ or GND, $I_O = 0$; $V_{CCA} = 1.08\text{V}$ to 3.6V ; $V_{CCB} = 1.08\text{V}$ to 3.6V			16	μA
C_i	Control inputs	$V_I = 3.3\text{V}$ or GND; $V_{CCA} = 3.3\text{V}$; $V_{CCB} = 3.3\text{V}$			4.5	pF
C_{io}	A or B port	$V_O = 3.3\text{V}$ or GND; $V_{CCA} = 3.3\text{V}$; $V_{CCB} = 3.3\text{V}$			5.1	pF

(1) V_{CCO} is the V_{CC} associated with the output port.

(2) V_{CCI} is the V_{CC} associated with the input port.

(3) For I/O ports, the parameter I_{OZ} includes the input leakage current.

5.6 Switching Characteristics: $V_{CCA} = 1.2V \pm 0.12V$

over recommended operating free-air temperature range (for parameter descriptions, see [Figure 6-1](#))

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CCB}	TYP	UNIT
t_{PLH} , t_{PHL}	A	B	$V_{CCB} = 1.2V \pm 0.12V$	3.1	ns
			$V_{CCB} = 1.5V \pm 0.1V$	2.6	
			$V_{CCB} = 1.8V \pm 0.15V$	2.5	
			$V_{CCB} = 2.5V \pm 0.2V3$	3	
			$V_{CCB} = 3.3V \pm 0.3V$	3.5	
t_{PLH} , t_{PHL}	B	A	$V_{CCB} = 1.2V \pm 0.12V$	3.1	ns
			$V_{CCB} = 1.5V \pm 0.1V$	2.7	
			$V_{CCB} = 1.8V \pm 0.15V$	2.5	
			$V_{CCB} = 2.5V \pm 0.2V$	2.4	
			$V_{CCB} = 3.3V \pm 0.3V$	2.3	
t_{PZH} , t_{PZL}	$\overline{OE}$	A	$V_{CCB} = 1.2V \pm 0.12V$	5.3	ns
			$V_{CCB} = 1.5V \pm 0.1V$	5.3	
			$V_{CCB} = 1.8V \pm 0.15V$	5.3	
			$V_{CCB} = 2.5V \pm 0.2V$	5.3	
			$V_{CCB} = 3.3V \pm 0.3V$	5.3	
t_{PZH} , t_{PZL}	$\overline{OE}$	B	$V_{CCB} = 1.2V \pm 0.12V$	5.1	ns
			$V_{CCB} = 1.5V \pm 0.1V$	4	
			$V_{CCB} = 1.8V \pm 0.15V$	3.5	
			$V_{CCB} = 2.5V \pm 0.2V$	3.2	
			$V_{CCB} = 3.3V \pm 0.3V$	3.1	
t_{PHZ} , t_{PLZ}	$\overline{OE}$	A	$V_{CCB} = 1.2V \pm 0.12V$	4.8	ns
			$V_{CCB} = 1.5V \pm 0.1V$	4.8	
			$V_{CCB} = 1.8V \pm 0.15V$	4.8	
			$V_{CCB} = 2.5V \pm 0.2V$	4.8	
			$V_{CCB} = 3.3V \pm 0.3V$	4.8	
t_{PHZ} , t_{PLZ}	$\overline{OE}$	B	$V_{CCB} = 1.2V \pm 0.12V$	4.7	ns
			$V_{CCB} = 1.5V \pm 0.1V$	4	
			$V_{CCB} = 1.8V \pm 0.15V$	4.1	
			$V_{CCB} = 2.5V \pm 0.2V$	4.3	
			$V_{CCB} = 3.3V \pm 0.3V$	5.1	

5.7 Switching Characteristics, $V_{CCA} = 1.5V \pm 0.1V$

over temperature range $-40^{\circ}C$ to $+125^{\circ}C$ (for parameter descriptions, see [Figure 6-1](#))

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CCB}	MIN	TYP	MAX	UNIT
t_{PHL}, t_{PLH}	A	B	$V_{CCB} = 1.2V \pm 0.12V$		4.2		ns
			$V_{CCB} = 1.5V \pm 0.1V$	2.2		5.7	
			$V_{CCB} = 1.8V \pm 0.15V$	2.0		4.7	
			$V_{CCB} = 2.5V \pm 0.2V$	1.7		3.8	
			$V_{CCB} = 3.3V \pm 0.3V$	1.5		3.4	
t_{PLH}, t_{PHL}	B	A	$V_{CCB} = 1.2V \pm 0.12V$		4.6		ns
			$V_{CCB} = 1.5V \pm 0.1V$	2.1		5.7	
			$V_{CCB} = 1.8V \pm 0.15V$	1.9		5.1	
			$V_{CCB} = 2.5V \pm 0.2V$	1.7		4.2	
			$V_{CCB} = 3.3V \pm 0.3V$	1.6		3.8	
t_{PZH}, t_{PZL}	$\overline{OE}$	A	$V_{CCB} = 1.2V \pm 0.12V$		5.8		ns
			$V_{CCB} = 1.5V \pm 0.1V$	3.8		10.6	
			$V_{CCB} = 1.8V \pm 0.15V$	3.8		10.7	
			$V_{CCB} = 2.5V \pm 0.2V$	3.7		10.6	
			$V_{CCB} = 3.3V \pm 0.3V$	3.7		10.5	
t_{PZH}, t_{PZL}	$\overline{OE}$	B	$V_{CCB} = 1.2V \pm 0.12V$		8.7		ns
			$V_{CCB} = 1.5V \pm 0.1V$	3.9		10.8	
			$V_{CCB} = 1.8V \pm 0.15V$	3.5		9.5	
			$V_{CCB} = 2.5V \pm 0.2V$	3.2		8.3	
			$V_{CCB} = 3.3V \pm 0.3V$	3.1		8.0	
t_{PHZ}, t_{PLZ}	$\overline{OE}$	A	$V_{CCB} = 1.2V \pm 0.12V$		5.6		ns
			$V_{CCB} = 1.5V \pm 0.1V$	3.9		9.4	
			$V_{CCB} = 1.8V \pm 0.15V$	3.9		9.4	
			$V_{CCB} = 2.5V \pm 0.2V$	3.9		9.4	
			$V_{CCB} = 3.3V \pm 0.3V$	3.9		9.4	
t_{PHZ}, t_{PLZ}	$\overline{OE}$	B	$V_{CCB} = 1.2V \pm 0.12V$		8.6		ns
			$V_{CCB} = 1.5V \pm 0.1V$	4.6		11.0	
			$V_{CCB} = 1.8V \pm 0.15V$	4.6		10.6	
			$V_{CCB} = 2.5V \pm 0.2V$	3.7		8.9	
			$V_{CCB} = 3.3V \pm 0.3V$	4.2		9.4	

5.8 Switching Characteristics: $V_{CCA} = 1.8V \pm 0.15V$

over temperature range -40 °C to +125 °C (for parameter descriptions, see [Figure 6-1](#))

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CCB}	MIN	TYP	MAX	UNIT
t_{PLH}, t_{PHL}	A	B	$V_{CCB} = 1.2V \pm 0.12V$		3.8		ns
			$V_{CCB} = 1.5V \pm 0.1V$	2.1		5.1	
			$V_{CCB} = 1.8V \pm 0.15V$	2.0		4.2	
			$V_{CCB} = 2.5V \pm 0.2V$	1.6		3.1	
			$V_{CCB} = 3.3V \pm 0.3V$	1.4		2.9	
t_{PLH}, t_{PHL}	B	A	$V_{CCB} = 1.2V \pm 0.12V$		4.2		ns
			$V_{CCB} = 1.5V \pm 0.1V$	2.2		4.7	
			$V_{CCB} = 1.8V \pm 0.15V$	2.0		4.2	
			$V_{CCB} = 2.5V \pm 0.2V$	1.8		3.7	
			$V_{CCB} = 3.3V \pm 0.3V$	1.7		3.3	
t_{PZH}, t_{PZL}	$\overline{OE}$	A	$V_{CCB} = 1.2V \pm 0.12V$		4.5		ns
			$V_{CCB} = 1.5V \pm 0.1V$	3.4		7.7	
			$V_{CCB} = 1.8V \pm 0.15V$	3.4		7.7	
			$V_{CCB} = 2.5V \pm 0.2V$	3.3		7.7	
			$V_{CCB} = 3.3V \pm 0.3V$	3.4		7.6	
t_{PZH}, t_{PZL}	$\overline{OE}$	B	$V_{CCB} = 1.2V \pm 0.12V$		8.0		ns
			$V_{CCB} = 1.5V \pm 0.1V$	3.9		9.1	
			$V_{CCB} = 1.8V \pm 0.15V$	3.4		7.9	
			$V_{CCB} = 2.5V \pm 0.2V$	3.0		6.6	
			$V_{CCB} = 3.3V \pm 0.3V$	2.9		6.2	
t_{PHZ}, t_{PLZ}	$\overline{OE}$	A	$V_{CCB} = 1.2V \pm 0.12V$		5.3		ns
			$V_{CCB} = 1.5V \pm 0.1V$	4.1		7.9	
			$V_{CCB} = 1.8V \pm 0.15V$	4.1		8.0	
			$V_{CCB} = 2.5V \pm 0.2V$	4.1		8.0	
			$V_{CCB} = 3.3V \pm 0.3V$	4.1		8.0	
t_{PHZ}, t_{PLZ}	$\overline{OE}$	B	$V_{CCB} = 1.2V \pm 0.12V$		7.7		ns
			$V_{CCB} = 1.5V \pm 0.1V$	4.5		9.4	
			$V_{CCB} = 1.8V \pm 0.15V$	4.6		9.1	
			$V_{CCB} = 2.5V \pm 0.2V$	3.9		7.6	
			$V_{CCB} = 3.3V \pm 0.3V$	4.3		8.1	

Switching Characteristics, $V_{CCA} = 2.5V \pm 0.2V$ **5.9 Switching Characteristics: $V_{CCB} = 2.5V \pm 0.2V$** over temperature range $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$ (for parameter descriptions, see [Figure 6-1](#))

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CCB}	MIN	TYP	MAX	UNIT
t_{PLH}, t_{PHL}	A	B	$V_{CCB} = 1.2V \pm 0.12V$		3.3		ns
			$V_{CCB} = 1.5V \pm 0.1V$	1.9		4.2	
			$V_{CCB} = 1.8V \pm 0.15V$	1.8		3.7	
			$V_{CCB} = 2.5V \pm 0.2V$	1.5		2.6	
			$V_{CCB} = 3.3V \pm 0.3V$	1.3		2.3	
t_{PLH}, t_{PHL}	B	A	$V_{CCB} = 1.2V \pm 0.12V$		3.6		ns
			$V_{CCB} = 1.5V \pm 0.1V$	1.8		3.8	
			$V_{CCB} = 1.8V \pm 0.15V$	1.6		3.1	
			$V_{CCB} = 2.5V \pm 0.2V$	1.5		2.6	
			$V_{CCB} = 3.3V \pm 0.3V$	1.5		2.5	
t_{PZH}, t_{PZL}	$\overline{OE}$	A	$V_{CCB} = 1.2V \pm 0.12V$		3.0		ns
			$V_{CCB} = 1.5V \pm 0.1V$	2.5		4.8	
			$V_{CCB} = 1.8V \pm 0.15V$	2.5		4.8	
			$V_{CCB} = 2.5V \pm 0.2V$	2.5		4.8	
			$V_{CCB} = 3.3V \pm 0.3V$	2.5		4.8	
t_{PZH}, t_{PZL}	$\overline{OE}$	B	$V_{CCB} = 1.2V \pm 0.12V$		7.0		ns
			$V_{CCB} = 1.5V \pm 0.1V$	3.5		7.4	
			$V_{CCB} = 1.8V \pm 0.15V$	3.1		6.1	
			$V_{CCB} = 2.5V \pm 0.2V$	2.6		4.9	
			$V_{CCB} = 3.3V \pm 0.3V$	2.4		4.4	
t_{PHZ}, t_{PLZ}	$\overline{OE}$	A	$V_{CCB} = 1.2V \pm 0.12V$		3.7		ns
			$V_{CCB} = 1.5V \pm 0.1V$	3.1		5.3	
			$V_{CCB} = 1.8V \pm 0.15V$	3.2		5.4	
			$V_{CCB} = 2.5V \pm 0.2V$	3.1		5.4	
			$V_{CCB} = 3.3V \pm 0.3V$	3.1		5.4	
t_{PHZ}	$\overline{OE}$	B	$V_{CCB} = 1.2V \pm 0.12V$		4.5		ns
			$V_{CCB} = 1.5V \pm 0.1V$	1.5		9.4	
			$V_{CCB} = 1.8V \pm 0.15V$	1.3		8.2	
			$V_{CCB} = 2.5V \pm 0.2V$	1.1		6.2	
			$V_{CCB} = 3.3V \pm 0.3V$	0.9		5.2	
t_{PLZ}	$\overline{OE}$	B	$V_{CCB} = 1.2V \pm 0.12V$		6.6		ns
			$V_{CCB} = 1.5V \pm 0.1V$	4.1		7.4	
			$V_{CCB} = 1.8V \pm 0.15V$	4.2		7.3	
			$V_{CCB} = 2.5V \pm 0.2V$	3.5		6.0	
			$V_{CCB} = 3.3V \pm 0.3V$	4.0		6.6	

5.10 Switching Characteristics: $V_{CCA} = 3.3V \pm 0.3V$

over temperature range -40 °C to +125 °C (for parameter descriptions, see [図 6-1](#))

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CCB}	MIN	TYP	MAX	UNIT
t_{PLH}, t_{PHL}	A	B	$V_{CCB} = 1.2V \pm 0.12V$		3.2		ns
			$V_{CCB} = 1.5V \pm 0.1V$	1.8		3.8	
			$V_{CCB} = 1.8V \pm 0.15V$	1.7		3.3	
			$V_{CCB} = 2.5V \pm 0.2V$	1.5		2.5	
			$V_{CCB} = 3.3V \pm 0.3V$	1.2		2.0	
t_{PLH}, t_{PHL}	B	A	$V_{CCB} = 1.2V \pm 0.12V$		3.4		ns
			$V_{CCB} = 1.5V \pm 0.1V$	1.7		3.4	
			$V_{CCB} = 1.8V \pm 0.15V$	1.5		2.9	
			$V_{CCB} = 2.5V \pm 0.2V$	1.3		2.9	
			$V_{CCB} = 3.3V \pm 0.3V$	1.2		2.0	
t_{PZH}, t_{PZL}	$\overline{OE}$	A	$V_{CCB} = 1.2V \pm 0.12V$		2.4		ns
			$V_{CCB} = 1.5V \pm 0.1V$	2.2		3.6	
			$V_{CCB} = 1.8V \pm 0.15V$	2.2		3.6	
			$V_{CCB} = 2.5V \pm 0.2V$	2.2		3.6	
			$V_{CCB} = 3.3V \pm 0.3V$	2.2		3.6	
t_{PZH}, t_{PZL}	$\overline{OE}$	B	$V_{CCB} = 1.2V \pm 0.12V$		6.7		ns
			$V_{CCB} = 1.5V \pm 0.1V$	3.2		6.7	
			$V_{CCB} = 1.8V \pm 0.15V$	2.8		5.4	
			$V_{CCB} = 2.5V \pm 0.2V$	2.4		4.2	
			$V_{CCB} = 3.3V \pm 0.3V$	2.2		3.7	
t_{PHZ}, t_{PLZ}	$\overline{OE}$	A	$V_{CCB} = 1.2V \pm 0.12V$		4.0		ns
			$V_{CCB} = 1.5V \pm 0.1V$	3.5		5.5	
			$V_{CCB} = 1.8V \pm 0.15V$	3.5		5.5	
			$V_{CCB} = 2.5V \pm 0.2V$	3.4		5.4	
			$V_{CCB} = 3.3V \pm 0.3V$	3.5		5.4	
t_{PHZ}, t_{PLZ}	$\overline{OE}$	B	$V_{CCB} = 1.2V \pm 0.12V$		6.3		ns
			$V_{CCB} = 1.5V \pm 0.1V$	4.0		6.6	
			$V_{CCB} = 1.8V \pm 0.15V$	4.0		6.5	
			$V_{CCB} = 2.5V \pm 0.2V$	3.3		5.3	
			$V_{CCB} = 3.3V \pm 0.3V$	3.7		5.9	

5.11 Operating Characteristics

 $T_A = 25^\circ\text{C}$

PARAMETER			TEST CONDITIONS	V _{CCA}	TYP	UNIT
C _{pdA} ⁽¹⁾	A to B	Outputs enabled	C _L = 0, f = 10MHz, t _r = t _f = 1ns	V _{CCA} = V _{CCB} = 1.2V	1	pF
				V _{CCA} = V _{CCB} = 1.5V	1	
				V _{CCA} = V _{CCB} = 1.8V	1	
				V _{CCA} =V _{CCB} = 2.5V	1.5	
				V _{CCA} = V _{CCB} = 3.3V	2	
		Outputs disabled	C _L = 0, f = 10MHz, t _r = t _f = 1ns	V _{CCA} = V _{CCB} = 1.2V	1	
				V _{CCA} = V _{CCB} = 1.5V		
				V _{CCA} = V _{CCB} = 1.8V		
				V _{CCA} =V _{CCB} = 2.5V		
				V _{CCA} = V _{CCB} = 3.3V		
	B to A	Outputs enabled	C _L = 0, f = 10MHz, t _r = t _f = 1ns	V _{CCA} = V _{CCB} = 1.2V	12	
				V _{CCA} = V _{CCB} = 1.5V	12.5	
				V _{CCA} = V _{CCB} = 1.8V	13	
				V _{CCA} =V _{CCB} = 2.5V	14	
				V _{CCA} = V _{CCB} = 3.3V	15	
		Outputs disabled	C _L = 0, f = 10MHz, t _r = t _f = 1ns	V _{CCA} = V _{CCB} = 1.2V	1	
				V _{CCA} = V _{CCB} = 1.5V		
				V _{CCA} = V _{CCB} = 1.8V		
				V _{CCA} =V _{CCB} = 2.5V		
				V _{CCA} = V _{CCB} = 3.3V		
C _{pdB} ⁽¹⁾	A to B	Outputs enabled	C _L = 0, f = 10MHz, t _r = t _f = 1ns	V _{CCA} = V _{CCB} = 1.2V	12	pF
				V _{CCA} = V _{CCB} = 1.5V	12.5	
				V _{CCA} = V _{CCB} = 1.8V	13	
				V _{CCA} =V _{CCB} = 2.5V	14	
				V _{CCA} = V _{CCB} = 3.3V	15	
		Outputs disabled	C _L = 0, f = 10MHz, t _r = t _f = 1ns	V _{CCA} = V _{CCB} = 1.2V	1	
				V _{CCA} = V _{CCB} = 1.5V		
				V _{CCA} = V _{CCB} = 1.8V		
				V _{CCA} =V _{CCB} = 2.5V		
				V _{CCA} = V _{CCB} = 3.3V		
	B to A	Outputs enabled	C _L = 0, f = 10MHz, t _r = t _f = 1ns	V _{CCA} = V _{CCB} = 1.2V	1	
				V _{CCA} = V _{CCB} = 1.5V	1	
				V _{CCA} = V _{CCB} = 1.8V	1	
				V _{CCA} =V _{CCB} = 2.5V	1	
				V _{CCA} = V _{CCB} = 3.3V	2	
		Outputs disabled	C _L = 0, f = 10MHz, t _r = t _f = 1ns	V _{CCA} = V _{CCB} = 1.2V	1	
				V _{CCA} = V _{CCB} = 1.5V		
				V _{CCA} = V _{CCB} = 1.8V		
				V _{CCA} =V _{CCB} = 2.5V		
				V _{CCA} = V _{CCB} = 3.3V		

(1) Power dissipation capacitance per transceiver

5.12 Typical Characteristics

$T_A = 25^\circ\text{C}$

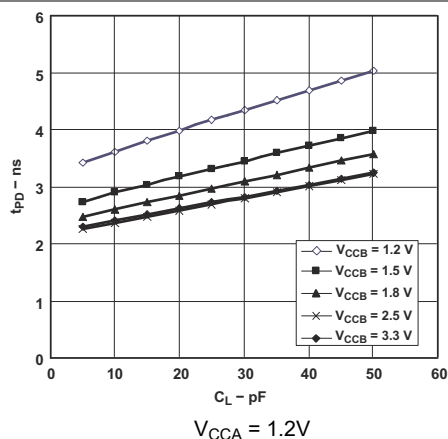


図 5-1. Typical Propagation Delay (A to B) vs Load Capacitance

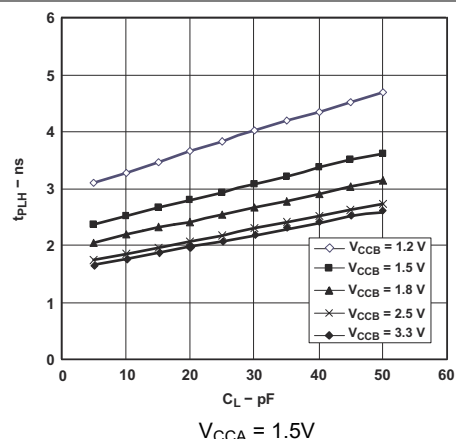


図 5-2. Typical Propagation Delay (A to B) vs Load Capacitance

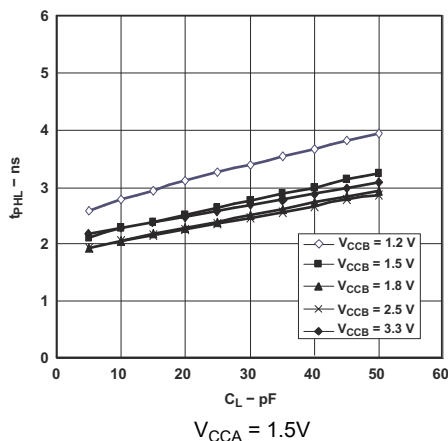


図 5-3. Typical Propagation Delay (A to B) vs Load Capacitance

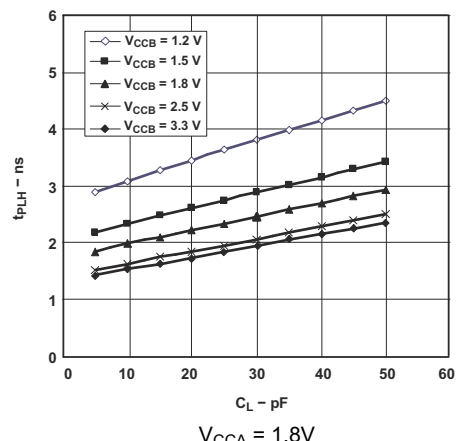


図 5-4. Typical Propagation Delay (A to B) vs Load Capacitance

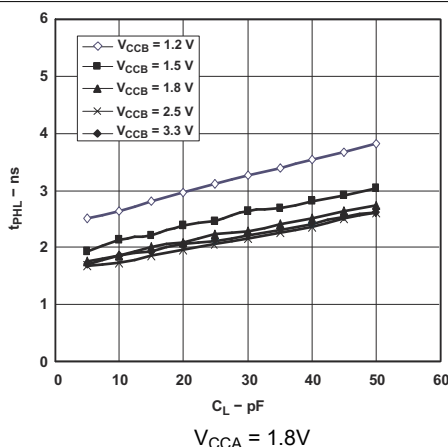


図 5-5. Typical Propagation Delay (A to B) vs Load Capacitance

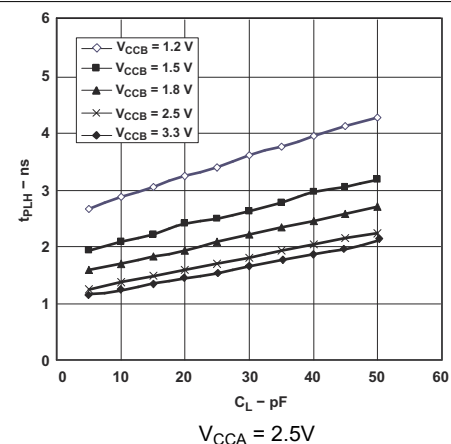


図 5-6. Typical Propagation Delay (A to B) vs Load Capacitance

5.12 Typical Characteristics (continued)

$T_A = 25^\circ\text{C}$

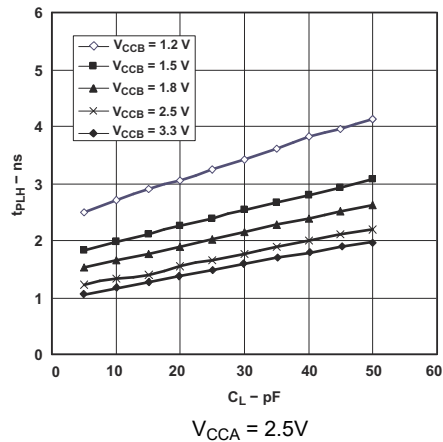


Figure 5-7. Typical Propagation Delay (A to B) vs Load Capacitance

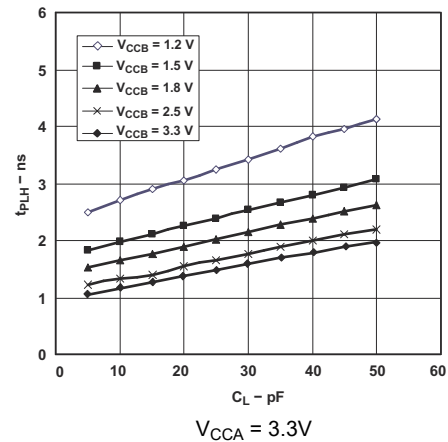


Figure 5-8. Typical Propagation Delay (A to B) vs Load Capacitance

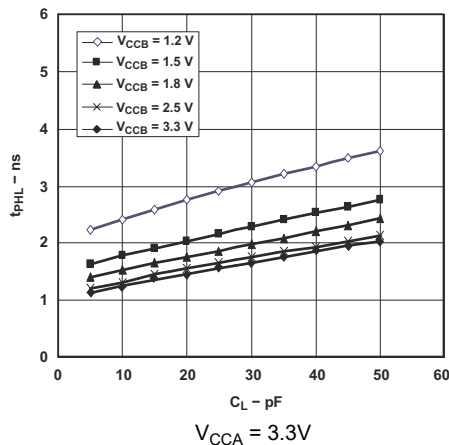


Figure 5-9. Typical Propagation Delay (A to B) vs Load Capacitance

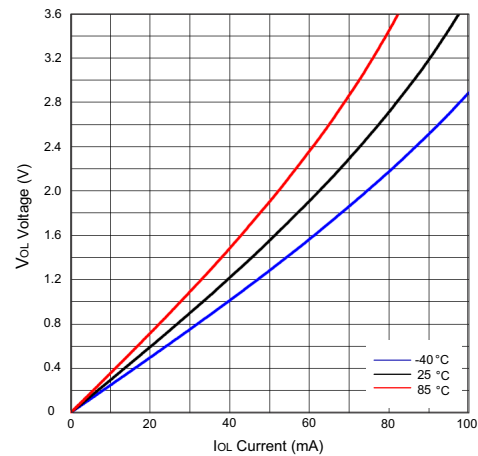


Figure 5-10. Low-Level Output Voltage (V_{OL}) vs Low-Level Current (I_{OL})

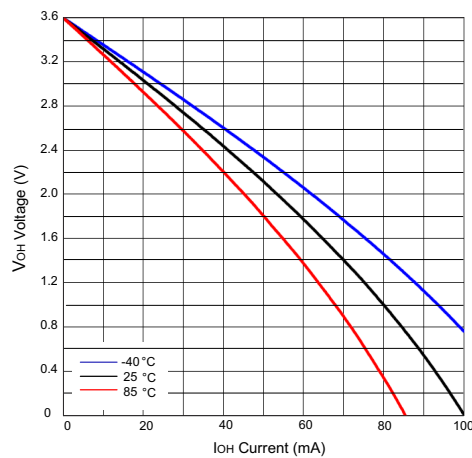
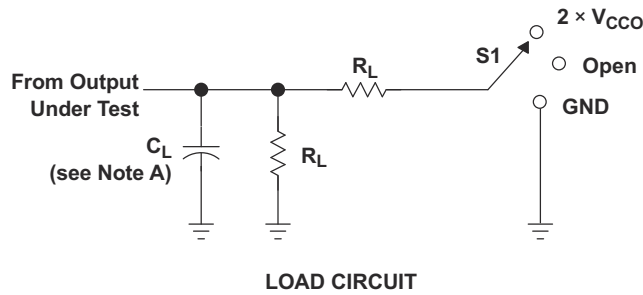


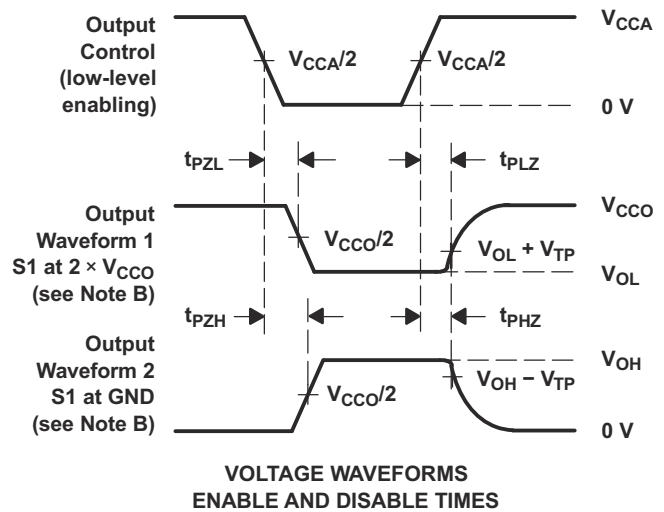
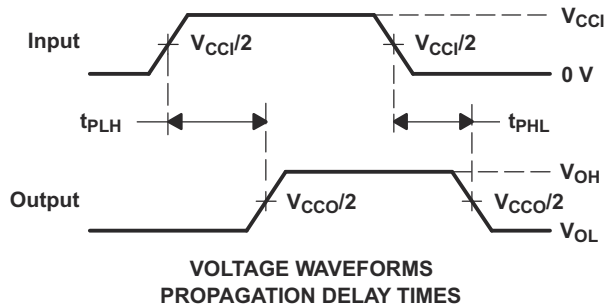
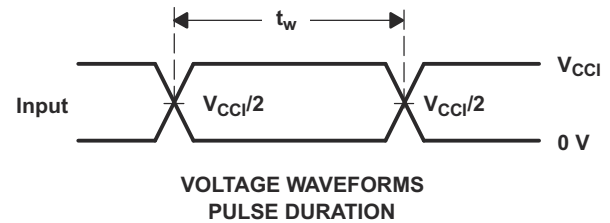
Figure 5-11. High-Level Output Voltage (V_{OH}) vs High-Level Current (I_{OH})

6 Parameter Measurement Information



TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	$2 \times V_{CCO}$
t_{PHZ}/t_{PZH}	GND

V_{CCO}	C_L	R_L	V_{TP}
1.2 V	15 pF	2 k Ω	0.1 V
1.5 V $\pm$ 0.1 V	15 pF	2 k Ω	0.1 V
1.8 V $\pm$ 0.15 V	15 pF	2 k Ω	0.15 V
2.5 V $\pm$ 0.2 V	15 pF	2 k Ω	0.15 V
3.3 V $\pm$ 0.3 V	15 pF	2 k Ω	0.3 V



- NOTES:
- C_L includes probe and jig capacitance.
 - Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
 - All input pulses are supplied by generators having the following characteristics: $PRR \leq 10$ MHz, $Z_O = 50 \Omega$, $dv/dt \geq 1$ V/ns.
 - The outputs are measured one at a time, with one transition per measurement.
 - t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 - t_{PZL} and t_{PZH} are the same as t_{en} .
 - t_{PLH} and t_{PHL} are the same as t_{pd} .
 - V_{CCI} is the V_{CC} associated with the input port.
 - V_{CCO} is the V_{CC} associated with the output port.

图 6-1. Load and Circuit and Voltage Waveforms

7 Detailed Description

7.1 Overview

The SN74AVC4T774-Q1 is a 4-bit, dual-supply noninverting bidirectional voltage level translation device. Ax pins and control pins (DIR1, DIR2, DIR3, DIR4 and $\overline{OE}$) are supported by V_{CCA} , and Bx pins are supported by V_{CCB} . The A port is able to accept I/O voltages ranging from 1.08V to 3.6V, while the B port can accept I/O voltages from 1.08V to 3.6V. A high on DIR allows data transmission from Ax to Bx and a low on DIR allows data transmission from Bx to Ax when $\overline{OE}$ is set to low. When $\overline{OE}$ is set to high, both Ax and Bx pins are in the high-impedance state.

7.2 Functional Block Diagram

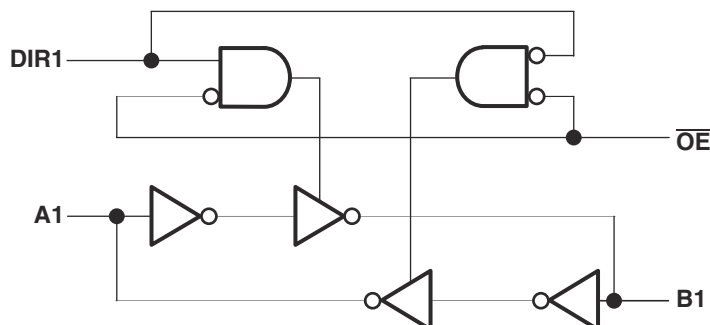


図 7-1. Logic Diagram (Positive Logic) of SN74AVC4T774-Q1

7.3 Feature Description

7.3.1 Fully Configurable Dual-Rail Design

Both V_{CCA} and V_{CCB} can be supplied at any voltage between 1.08V and 3.6V; thus, making the device suitable for translating between any of the low voltage nodes (1.2V, 1.8V, 2.5V, and 3.3V).

7.3.2 Supports High Speed Translation

The SN74AVC4T774-Q1 device can support high data rate applications. The translated signal data rate can be up to 500Mbps when the signal is translated from 1.8V to 3.3V.

7.3.3 I_{off} Supports Partial-Power-Down Mode Operation

I_{off} prevents backflow current by disabling I/O output circuits when the device is in partial-power-down mode.

7.4 Device Functional Modes

表 7-1 lists the functional modes of the SN74AVC4T774-Q1 device.

表 7-1. Function Table (Each Bit)

CONTROL INPUTS		OUTPUT CIRCUITS ⁽¹⁾		OPERATION
$\overline{OE}$	DIR	A PORT	B PORT	
L	L	Enabled	Hi-Z	B data to A bus
L	H	Hi-Z	Enabled	A data to B bus
H	X	Hi-Z	Hi-Z	Isolation

(1) Input circuits of the data I/Os are always active.

8 Application and Implementation

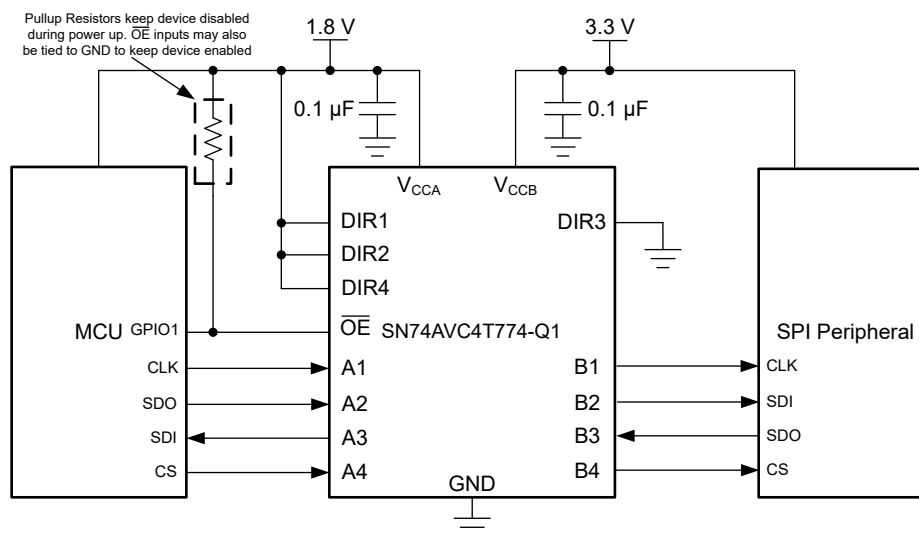
注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

8.1 Application Information

The SN74AVC4T774-Q1 device can be used in level-translation applications for interfacing devices or systems operating at different interface voltages with one another. The SN74AVC4T774-Q1 device is ideal for use in applications where a push-pull driver is connected to the data I/Os. The maximum data rate can be up to 500Mbps when the device translates a signal from 1.8V to 3.3V.

8.2 Typical Application



8-1. Typical Application Diagram

8.2.1 Design Requirements

表 8-1 lists the parameters for this design example.

表 8-1. Design Parameters

DESIGN PARAMETER	EXAMPLE VALUE
Input voltage range	1.2V
Output voltage range	3.3V

8.2.2 Detailed Design Procedure

To begin the design process, determine the following:

- Input voltage range
 - Use the supply voltage of the device that is driving the SN74AVC4T774-Q1 device to determine the input voltage range. For a valid logic high, the value must exceed the V_{IH} of the input port. For a valid logic low, the value must be less than the V_{IL} of the input port. For this example, the input voltage is 1.2V.
- Output voltage range
 - Use the supply voltage of the device that the SN74AVC4T774-Q1 device is driving to determine the output voltage range. For this example, the output voltage is 3.3V.

8.2.3 Application Curve

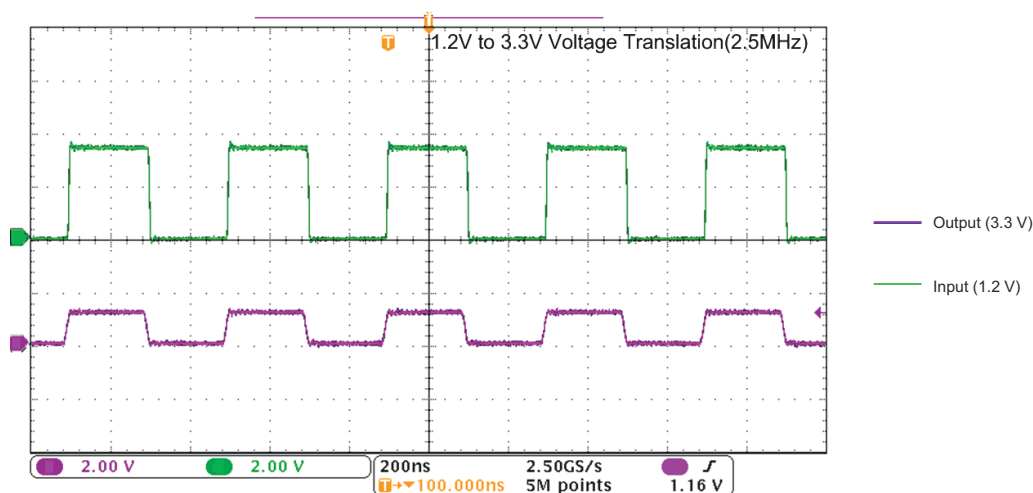


図 8-2. Translation Up (1.2V to 3.3V) at 2.5MHz

8.3 Power Supply Recommendations

The SN74AVC4T774-Q1 device uses two separate configurable power-supply rails: V_{CCA} and V_{CCB} . V_{CCA} accepts any supply voltage from 1.08V to 3.6V, and V_{CCB} accepts any supply voltage from 1.08V to 3.6V. The A port and B port are designed to track V_{CCA} and V_{CCB} respectively, allowing for low-voltage bidirectional translation between any of the 1.2V, 1.5V, 1.8V, 2.5V, and 3.3V voltage nodes.

The output-enable ($\overline{OE}$) input circuit is designed so that it is supplied by V_{CCA} ; when the $\overline{OE}$ input is high, all outputs are placed in the high-impedance state. To place the outputs in the high-impedance state during power up or power down, tie the $\overline{OE}$ input pin to V_{CCA} through a pullup resistor and do not enable it until V_{CCA} and V_{CCB} are fully ramped and stable. The minimum value of the pullup resistor to V_{CCA} is determined by the current-sinking capability of the driver.

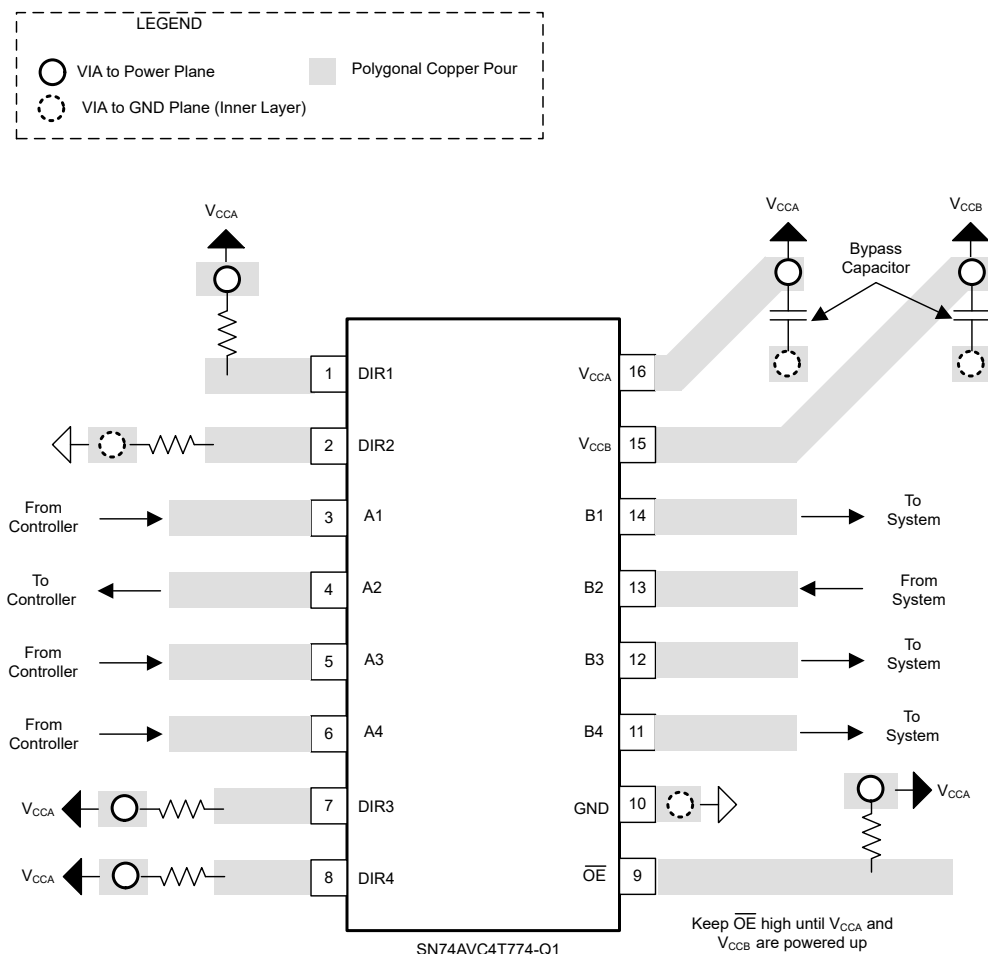
8.4 Layout

8.4.1 Layout Guidelines

For device reliability, the recommendation is to follow common printed-circuit board layout guidelines such as:

- Use bypass capacitors on power supplies.
- Use short trace lengths to avoid excessive loading.
- Place pads on the signal paths for loading capacitors or pullup resistors to help adjust rise and fall times of signals, depending on the system requirements.

8.4.2 Layout Example



8-3. SN74AVC4T774-Q1 PW Package Layout Diagram

9 Device and Documentation Support

9.1 Documentation Support

9.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, [IC Package Thermal Metrics](#)
- Texas Instruments, [Implications of Slow or Floating CMOS Inputs](#)

9.2 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、www.tij.co.jp のデバイス製品フォルダを開いてください。[通知] をクリックして登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取ることができます。変更の詳細については、改訂されたドキュメントに含まれている改訂履歴をご覧ください。

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9.6 用語集

[テキサス・インスツルメンツ用語集](#) この用語集には、用語や略語の一覧および定義が記載されています。

10 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Changes from Revision A (September 2024) to Revision B (December 2024)	Page
• 「概要」を更新.....	1
• Updated Pinout Diagrams.....	4
• Updated Pin Description.....	4
• Updated Overview.....	18
• Updated 図 7-1	18
• Updated 図 8-1	19
• Updated 図 8-3	21

Changes from Revision * (March 2024) to Revision A (September 2024)	Page
• ステータスを「事前情報」から「量産データ」に変更.....	1

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most-current data available for the designated device. This data is subject to change without notice and without revision of this document. For browser-based versions of this data sheet, see the left-hand navigation pane.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
74AVC4T774QDYRQ1	Active	Production	SOT-23-THIN (DYY) 16	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	WT774Q
74AVC4T774QDYRQ1.A	Active	Production	SOT-23-THIN (DYY) 16	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	WT774Q
74AVC4T774QPWRQ1	Active	Production	TSSOP (PW) 16	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	WT774Q
74AVC4T774QPWRQ1.A	Active	Production	TSSOP (PW) 16	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	WT774Q
74AVC4T774QWBQRQ1	Active	Production	WQFN (BQB) 16	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	WT774Q
74AVC4T774QWBQRQ1.A	Active	Production	WQFN (BQB) 16	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	WT774Q

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

⁽⁴⁾ **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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OTHER QUALIFIED VERSIONS OF SN74AVC4T774-Q1 :

- Catalog : [SN74AVC4T774](#)

NOTE: Qualified Version Definitions:

- Catalog - TI's standard catalog product

TAPE AND REEL INFORMATION



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
74AVC4T774QDYRQ1	SOT-23-THIN	DYY	16	3000	330.0	12.4	4.8	3.6	1.6	8.0	12.0	Q3
74AVC4T774QPWRQ1	TSSOP	PW	16	3000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
74AVC4T774QWBQRQ1	WQFN	BQB	16	3000	180.0	12.4	2.8	3.8	1.2	4.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
74AVC4T774QDYRQ1	SOT-23-THIN	DYY	16	3000	336.6	336.6	31.8
74AVC4T774QPWRQ1	TSSOP	PW	16	3000	356.0	356.0	35.0
74AVC4T774QWBQRQ1	WQFN	BQB	16	3000	210.0	185.0	35.0

GENERIC PACKAGE VIEW

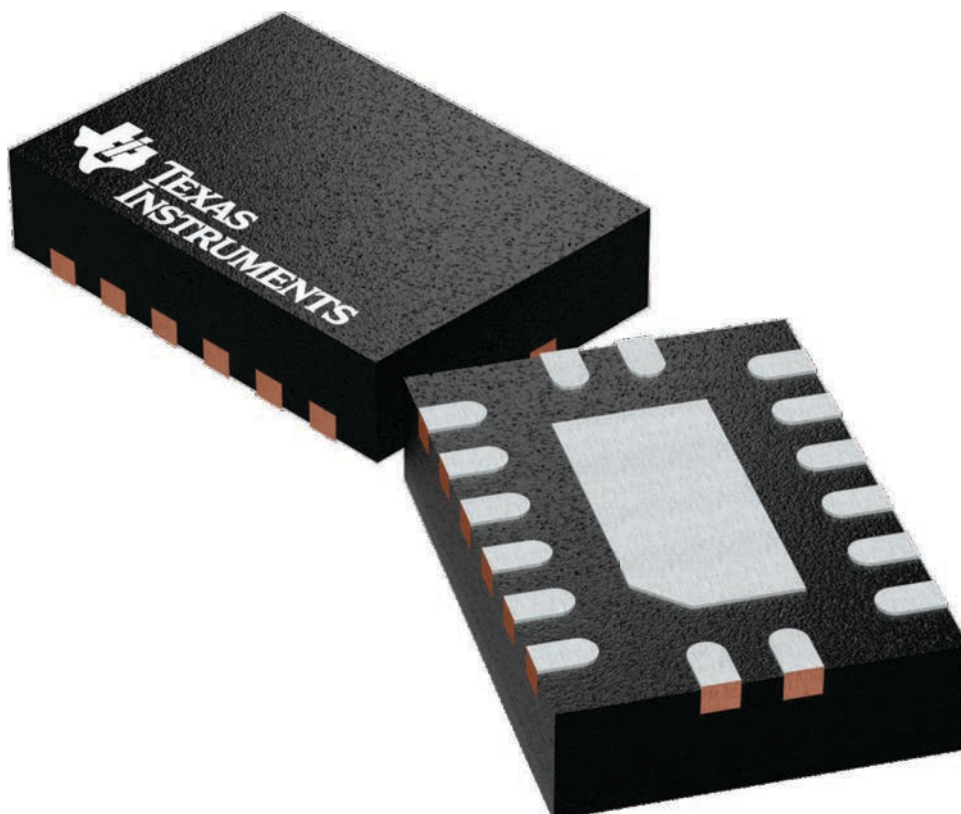
BQB 16

WQFN - 0.8 mm max height

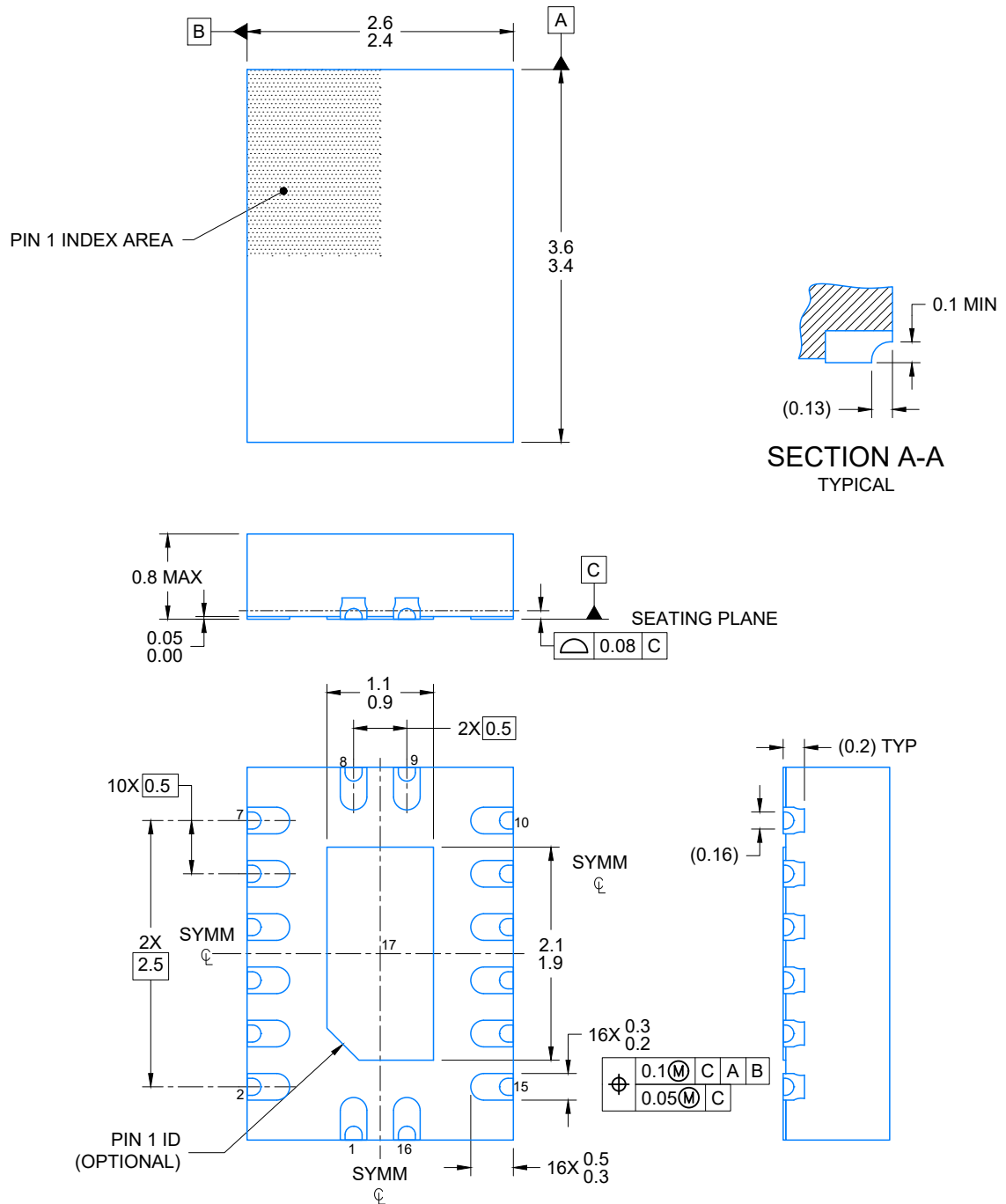
2.5 x 3.5, 0.5 mm pitch

PLASTIC QUAD FLATPACK - NO LEAD

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.



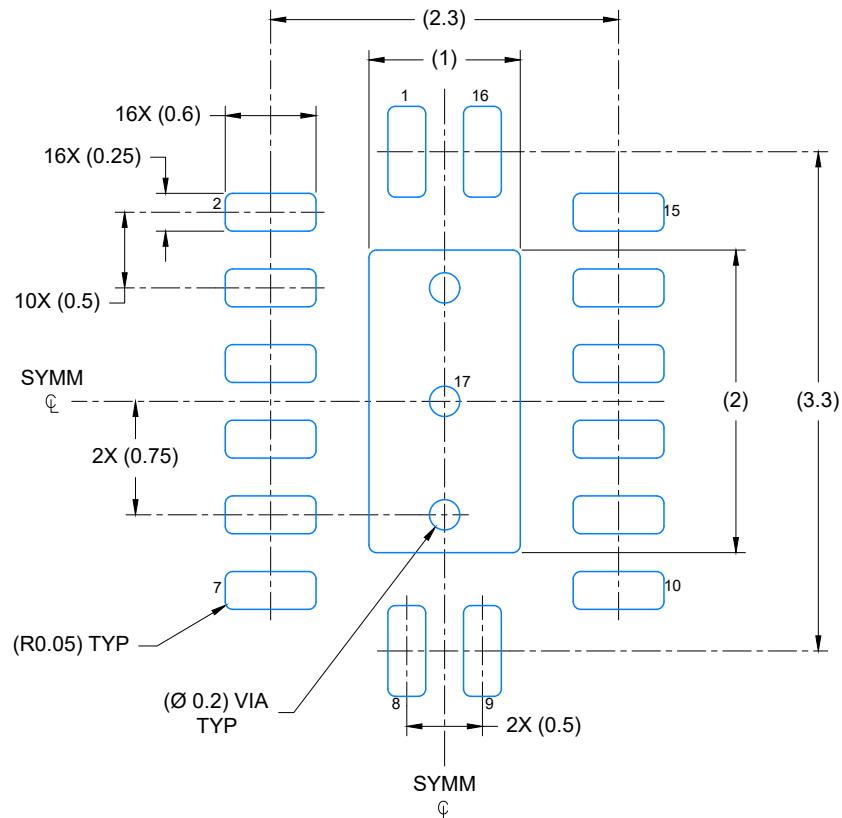
4226161/A



4226135/A 08/2020

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for optimal thermal and mechanical performance.

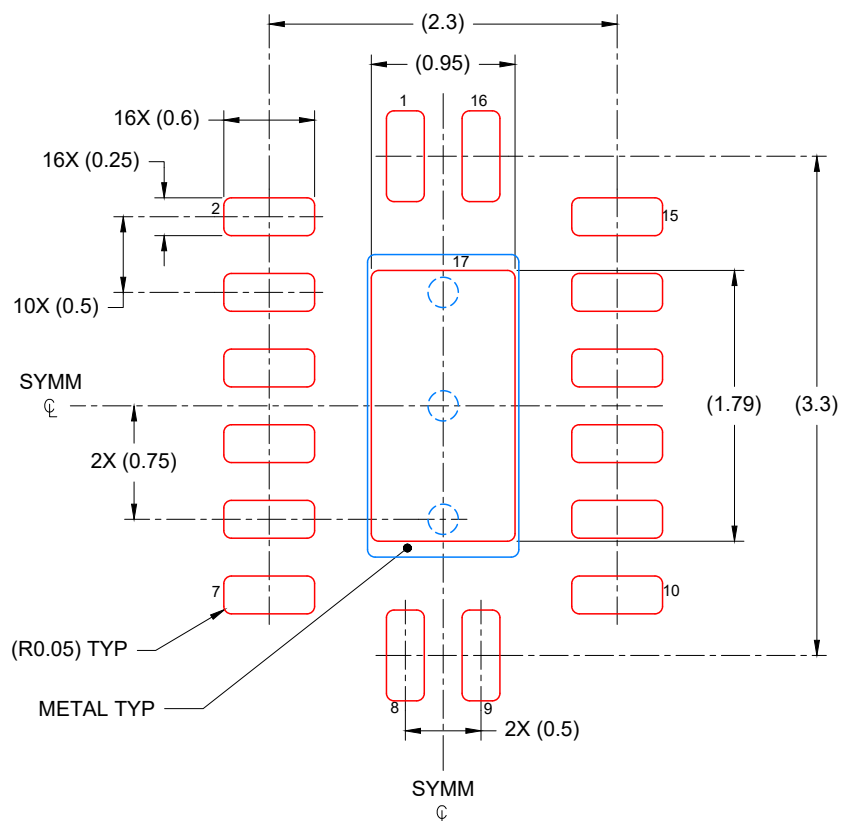


LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 20X

4226135/A 08/2020

NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/sluea271).
5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



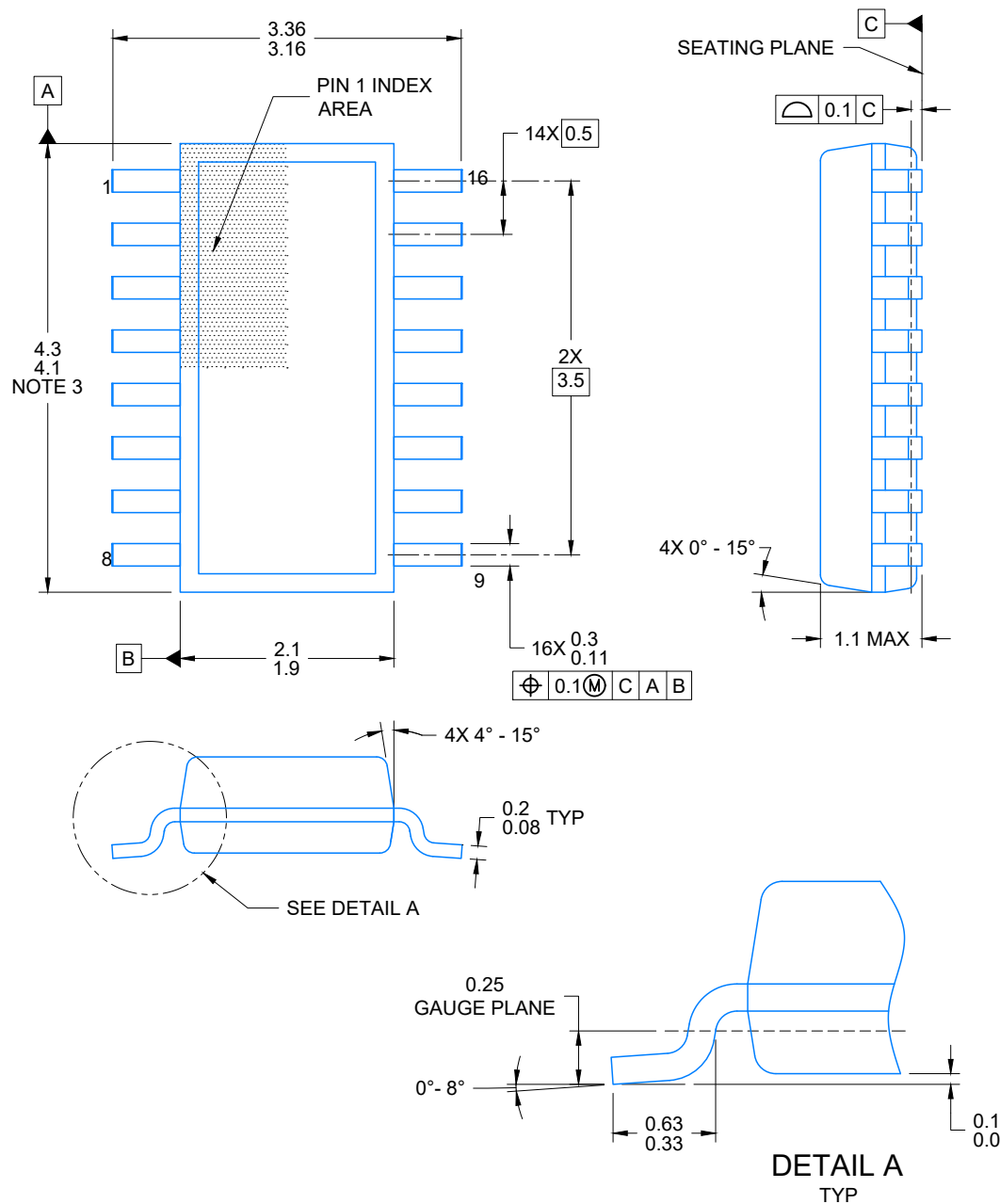
SOLDER PASTE EXAMPLE BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD
85% PRINTED COVERAGE BY AREA
SCALE: 20X

4226135/A 08/2020

NOTES: (continued)

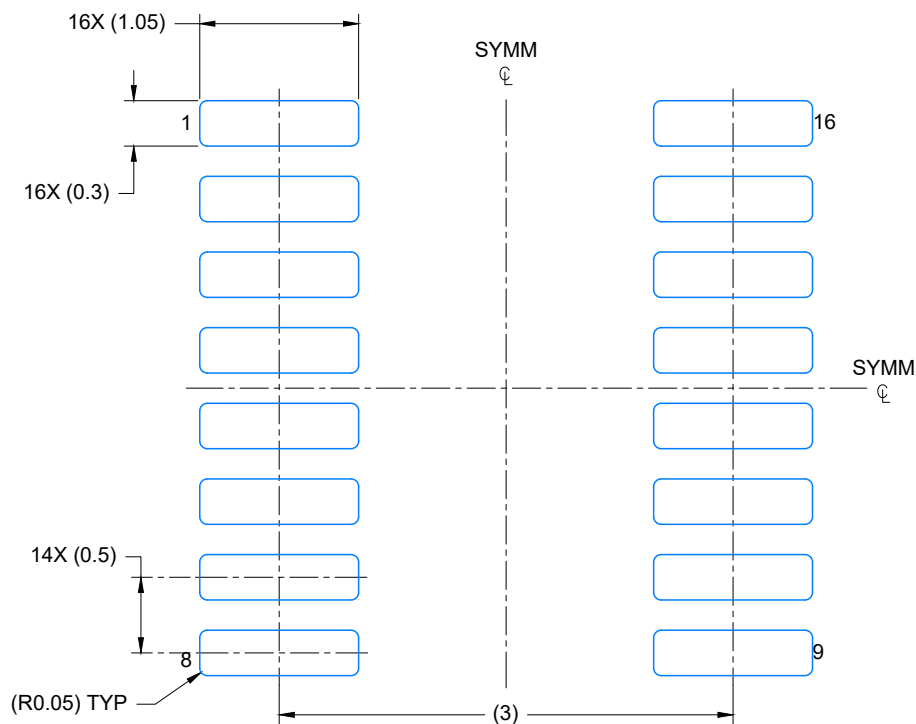
6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



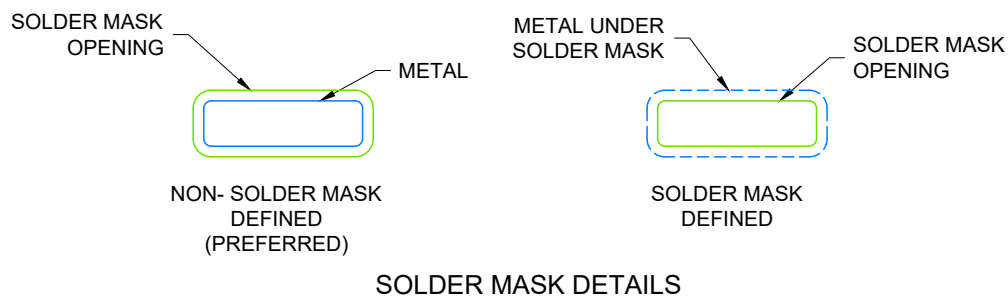
4224642/D 07/2024

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.50 per side.
5. Reference JEDEC Registration MO-345, Variation AA



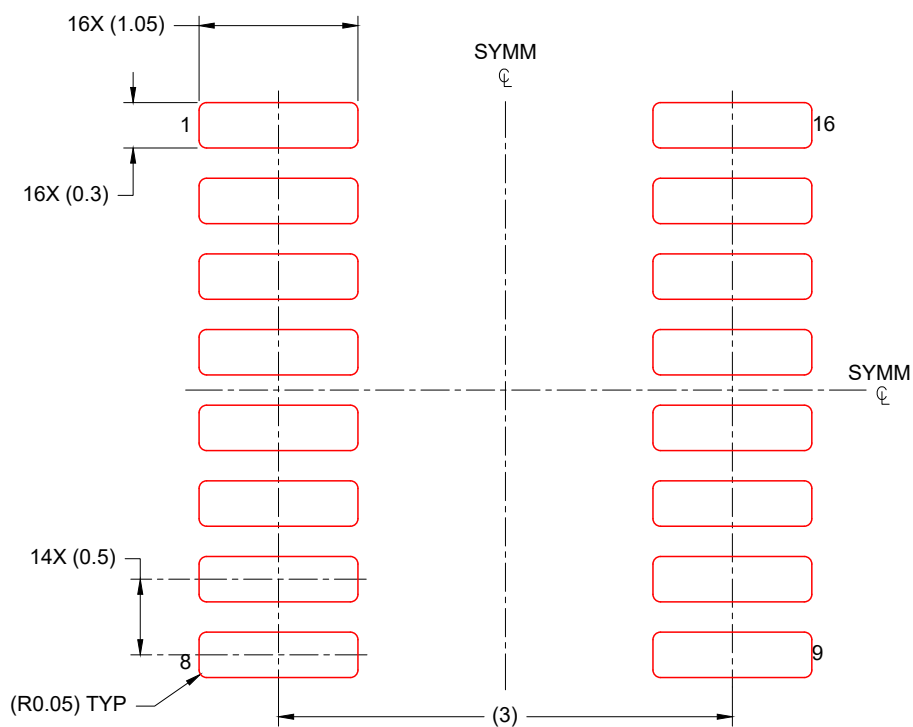
LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 20X



4224642/D 07/2024

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

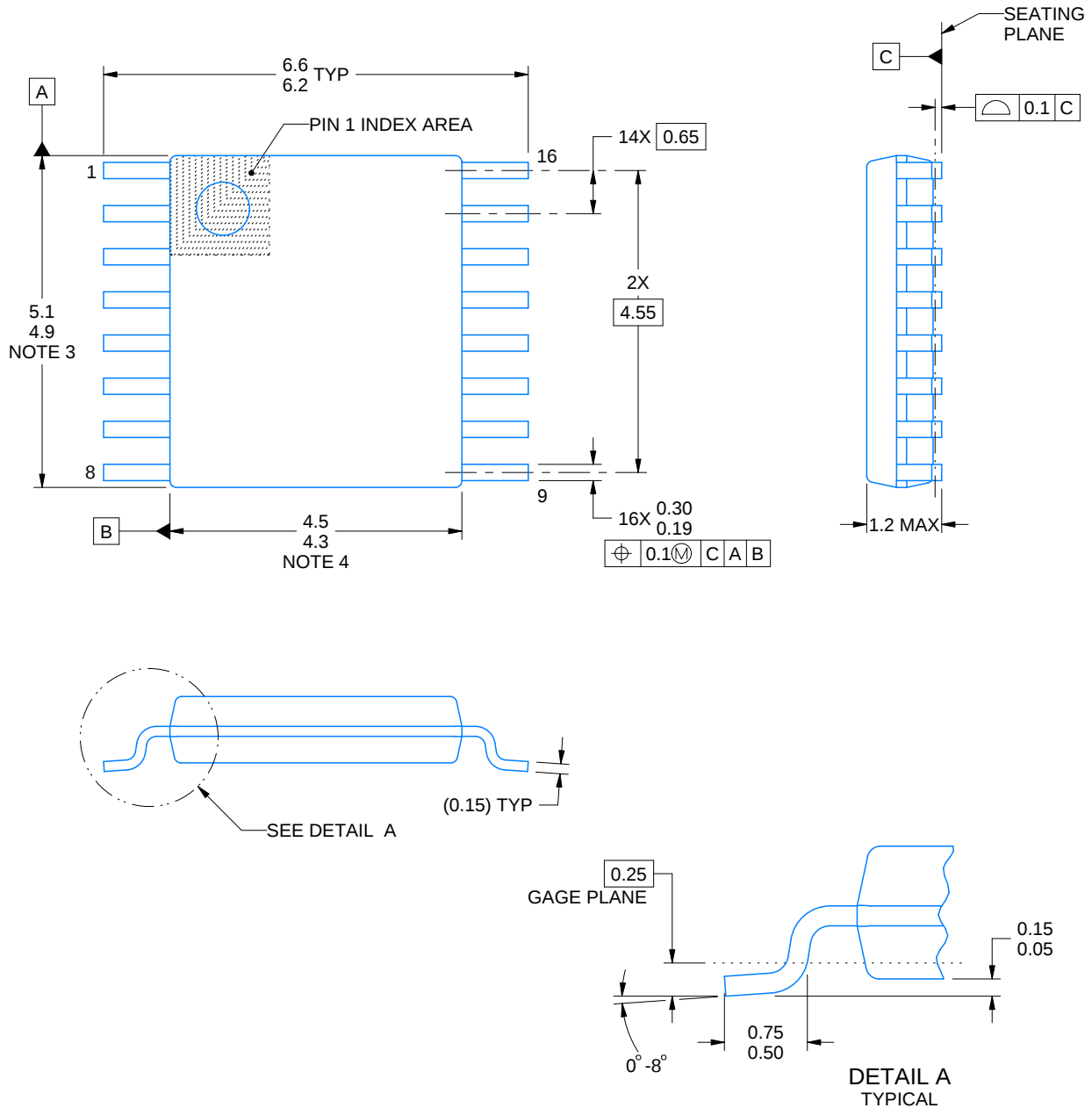
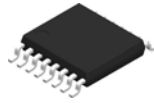


SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 20X

4224642/D 07/2024

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.



4220204/A 02/2017

NOTES:

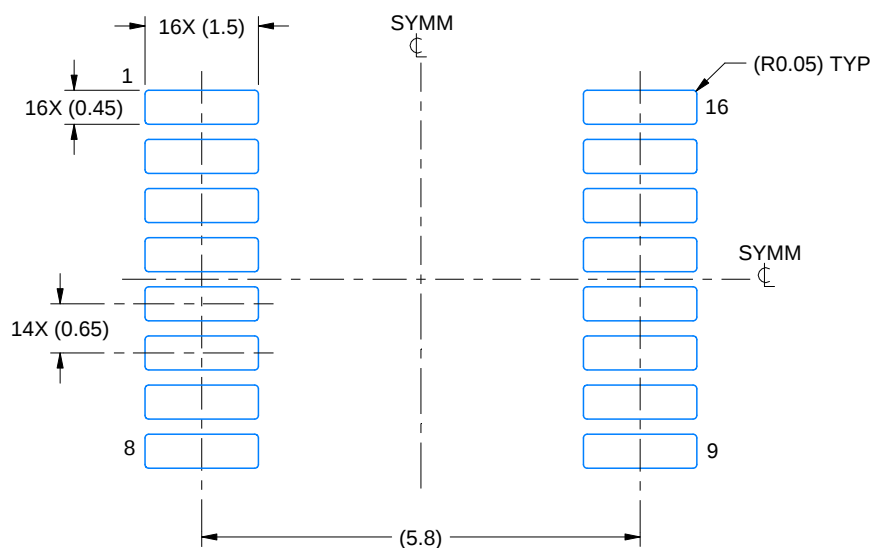
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.

EXAMPLE BOARD LAYOUT

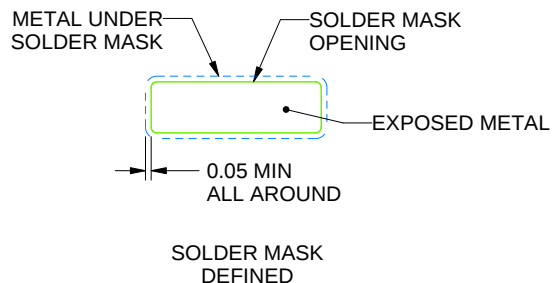
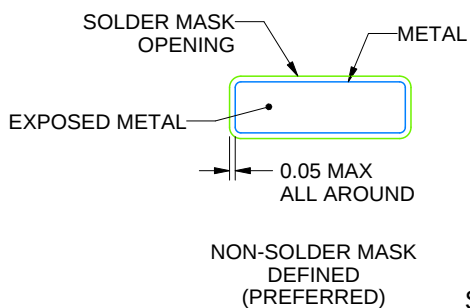
PW0016A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X



SOLDER MASK DETAILS

4220204/A 02/2017

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

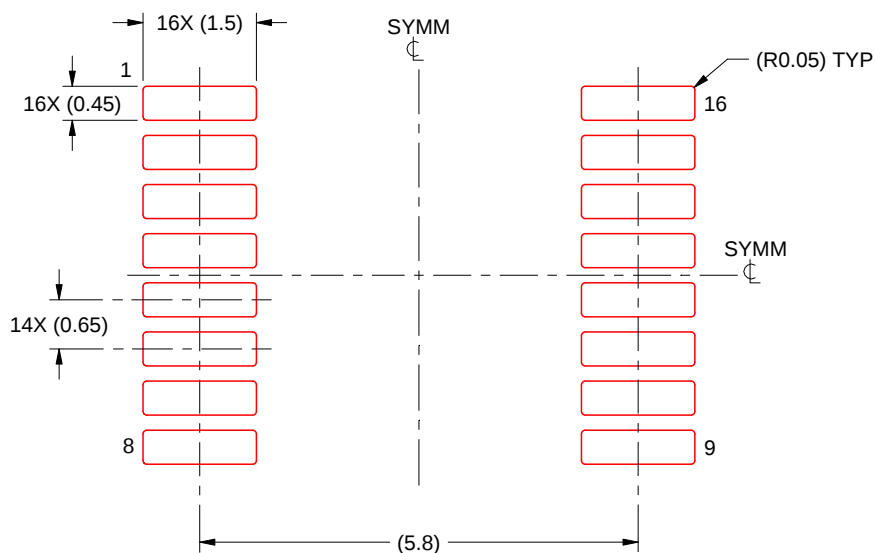
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

PW0016A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4220204/A 02/2017

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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